

Index

a

acetylene oligomers, 228
 AC modulation method, 160
 addition energy, 213, 249
 Adleman rational, 307
 alkanethiol-based junctions, 187
 alkanethiols, isotope labeling of, 162
 4-aminothiophenol (4-ATP), 151
 AND logic, 309, 313
 annealing process, 16
 anthraquinone (AQ), 301
 anthraquinone/hydroanthraquinone (AQ/H₂AQ), 300, 301
 archetypal folded luminogen molecule (Z)-o-BPTPE, 142
 aromatic stacking, 245, 246
 “atom-counting” approach, 119
 atomic force microscopy (AFM), 7, 10, 109, 130, 167, 213, 247, 376
 attenuation factor, 21, 23, 24, 167, 170, 238, 239
 Au–benzodifuran (BDF)–Au junctions, 190
 Au/bipyridyl-dinitro oligophenylenedithynylene dithiol molecule (BPDN-DT)/Au, 288
 Aviram–Ratner model, 259–261
 azobenzene-derivative molecules, 164

b

bare electron tunneling, 211
 1,4-benzenedithiol (BDT), 18, 129, 252, 279
 thermoelectricity properties of, 129

benzene-dominated chains, 230, 232–234
 Breit–Wigner formula, 215
 binary-state molecules, 291
 biological wires, 241–244
 biotin–avidin magnetic beads system, 308
 bistable [2]rotaxane R⁸⁺-totaxanes with graphene, 149
 1,4-bis[(5-tert-butyl-3-formyl-4-hydroxyphenyl)ethynyl]benzene, 305
 block copolymer (BCP), 56, 263
 Boolean logic, 306, 309, 310
 Borden formalism, 209
 Born–Oppenheimer approximation, 215
 break junction
 C₆₀-terminated SPM, 15
 EC-STM, 13
 electromigration, 32, 40
 nanotube-tip-based SPM, 14–15
 Breit–Wigner formula, 3
 buffer interlayer-based junction, 45, 62–65
 butadiyne-bridged porphyrin wires, 239

c

capillary tunnel junctions, 49–50
 carbon-based electrodes, 7, 34, 107–109, 281, 291, 334, 375
 carbon nanotube-based electrodes
 graphite, 107

- carbon nanotube-based electrodes
(*contd.*)
- pyrolyzed photoresist films, 108, 109
 - SWCNTs
 - electrical breakdown of, 94–98
 - lithography-defined oxidative cutting process, 98–102 - carbon nanotubes (CNTs), 14, 33, 93, 95–98, 189, 239–241
 - arc discharge, 239
 - chemical vapor deposition (CVD), 239
 - device architectures, 240, 241
 - electrolysis using graphite electrodes, 239
 - feature of, 239
 - laser ablation, 239
 - macromolecular systems, 239
 - molecular electronics, 239
- Carotene, 241, 243
- Catenene-based switches, 291–292
- charge transfer, in TTF–TCNQ system, 149–150
- chemical etching, 47, 65, 67, 114
- chemical logic gates, 312, 313
- chemically derived graphene (CDG), 64
- chemical soldering method, 116
- chemical stimuli triggered switch, 290–293
- click chemistry, 53–54, 60, 340, 377
- CMOS processing techniques, 115
- cobalt (II) phthalocyanine (CoPc)
- molecules, 274
- coherent tunneling, 102, 169, 214
- complementary metal–oxide–semiconductor (CMOS), 1, 113–115, 241, 375, 376, 379, 381
- conductance 2D auto-correlation histogram (C-2DACH), 193
- conducting probe atomic force microscopy (CP-AFM), 10, 130, 232
- conduction mechanisms, 166
- conductive polydiacetylene (PDA)
- nanowires, 116
- conjugated chains, 227–228
- conjugated porphyrin arrays, 237–239
- conventional sensors, 313
- coordination polymers, 237
- Coulomb blockade, 11, 16, 33, 38, 40, 125–128, 170, 217, 237, 249, 265, 279, 281
- Coulomb interaction, 189, 255, 256
- counter electrode (CE), 40, 42, 61, 68
- covalent bonding, 246, 334, 380
- crossbar architecture, 58
- crossbar method, 56
- crosswire method, 56
- C_{60} -terminated SPM break junction, 15
- cucurbit[8]uril (CB[8]) complexes, 149
- current–voltage characterization calculation, 217–221

d

- D–A diblock molecular system, 263–267
- dash-line lithography (DLL), 103–107, 376
- Datta–Paulsson (DP) model, 259, 262
- Debye screening length, 298
- density functional theory (DFT), 11, 17, 120, 123, 130, 164, 169, 215–217, 248
- destructive interference effects, 13
- destructive quantum-interference effects, 122
- detrapping processes, 27, 173, 178
- dialkylterthiophene/dialkylbenzene-tetracyanoethylene(TCNE) complex, 152
- diarylethene (DAE), 190, 251, 315
- 4,4'-dibenzenedithiol, thermoelectricity properties of, 129
- diblock dipyrimidinyldiphenyl molecule, 264, 265
- dielectrophoresis technique, 68
- dielectrophoretic method, 58
- Dip-pen nanolithography (DPN), 52

- dipyrimidinyl-diphenyl co-oligomer diode, 268
- direct *I-V* spectroscopy, 15
- DNA, 241
- DNA hybridization/polymorphism, 329–331
- DNA molecules, 94, 101, 102, 242, 243, 323
- DNA–protein interactions, 325, 326
- DNAzyme-based Cu²⁺ sensors, 325, 327
- double/triple bond-dominated backbones, 228
- doubly/triply fused porphyrins, 238
- D–σ–A and D–π–A system, 262–263
- D–σ–A molecular rectifiers, 259
- e**
- E-beam lithography technique, 31
- EC-STM break junction (EC-STM-BJ), 13, 283
- elastic scattering, 3, 69, 180, 181
- electrical breakdown, 33, 94–98, 103, 381
- electrical field induced switch, 285–286
- electrically driven single-photon emission, 131, 132
- electrical sensors, 313, 314
- electroburning process, 103
- electrochemical deposition junction, 40–43
- electrochemical gating, 283–284, 297, 299, 301
- electrochemically assisted mechanically controllable break junction (EC-MCBJ) technique, 141
- electrochemically-gated switch, 297–301
- electrode-molecule bonding, 225
- electroless gold plating (EGP), 41
- electroless plating rate, 42
- electromigration, 2, 282
- measurement, 126
- method, 34, 39, 40, 162, 182, 376
- process, 32–34, 36–40, 282, 377
- technique, 33, 35, 38–40, 181, 278, 279
- electromigration breakdown junction, 35
- device fabrication, 33, 34
- electromigration process, 37, 38
- feedback-controlled electromigration, 36, 37
- gap size control, 34, 35
- inelastic electron tunneling spectroscopy (IETS), 38
- Kondo effect, 39, 40
- self-breaking method, 35, 36
- surface-enhanced Raman spectroscopy (SERS), 38, 39
- electron-beam, 376
- evaporation/lithography, 61
- electron beam induced decomposition (EBID), 97
- electron beam lithography (EBL), 16, 21, 23–25, 33, 40, 51, 61
- electron-donating amine, 251
- electron-electron Coulomb repulsions, 215
- electronic devices, 1, 4, 7, 27, 37, 46, 47, 60, 64, 107, 119, 126, 137, 140, 157, 163, 173, 217, 226, 274, 280, 284, 290, 314
- electron-phonon coupling, 177, 214
- electron spin resonance (ESR), 276–277
- electron transport
- heating, 17–18
 - imaging, 16–17
 - mechanical forces, 18
 - mechanically controllable break junctions (MCBJs), 26
 - nanolithography, 18–19
 - optoelectronics, 17
 - stereoelectronics, 17
- electron transport mechanism
- electron-phonon interaction effects, 214–215
 - molecular junctions, 212–214
- electron trapping, 27

- electron-vibration interaction, in multichannel molecular junctions, 176
- elementary information, 314
- energy level alignment, 113, 185, 188, 250–252, 263, 294, 301, 333
- ensemble molecular junctions, 45
- buffer interlayer-based junction, 62–65
 - lift-and-float approach, 45–47
 - liquid metal contact, 47–50
 - nanopore and nanowell, 50–52
 - on-edge molecular junctions (OEMJs), 65–68
 - on-wire lithography (OWL), 52–54
 - self-aligned lithography, 60–62
 - suspended-wire molecular junctions (SWMJs), 68–71
 - transfer printing techniques, 54–60
- ethyne-bridged porphyrin wires, 239
- 4-ethynylbenzaldehyde, 114, 115
- Extended molecule, 215, 217, 220
- f**
- Fano factor, 171, 172, 175–177
- feedback-controlled electromigration (FCE) technique, 36, 37
- Fermi energy, 107, 122, 125, 212, 246, 249–252, 260, 261, 268, 378
- Fermi Golden rule, 214
- Fermi wavelength, 212
- ferrocene-alkanethiolate SAMs, rectification properties of, 169
- finite-difference time-domain (FDTD), 69
- first-principles modeling
- current-voltage characterization, 217–221
 - density functional theory (DFT), 215–217
- flicker noise, 172–173
- fluorescence resonance energy transfer (FRET), 309, 313
- 1/f noise, 173–175
- focused-ion-beam (FIB)
- etching, 94
 - lithography, 33
- Fowler–Nordheim (F-N) equation, 209
- tunneling, 166, 170, 187, 297
- fullerene-porphyrin complex, 150
- fused porphyrins, 238
- g**
- gap size control, 32, 34–37
- gate-controlled single-molecule diode, 272
- gate coupling efficiency factor, 34
- gate electrode, 23–25, 34, 68, 125, 129, 277, 282, 297, 302
- gear-coupling, 21, 22
- generation-recombination noise, 171–173
- gold electrodes, 42, 56, 66, 129, 236, 253, 256
- gold tunnel junctions, 375
- G-quadruplex structures, 242
- graphene, 64, 376, 380
- graphene-based electrodes
- dash-line lithography (DLL), 103–107
 - electroburning process, 103
- graphene-based single-molecule systems, 252
- graphene-molecule-graphene single molecule junctions (GMG-SMJs), 138
- graphene-molecule single-molecule junctions, 105, 294, 296
- graphene oxide (GO), 64
- graphite, 64, 101, 107, 109, 114, 239, 268
- Green formulism, 218
- Green function, 219, 220, 244
- h**
- Hamiltonian path problem (HPP), 307
- highest occupied molecular orbitals (HOMO), 11
- AR model, 259–261
- conjugated porphyrin arrays, 237
- coupling strength and transport mechanism, 249–250
- energy level alignment, 250–252

- gold electrodes, 256
 molecular conductance, 245
 molecular electronic levels, 279
 saturated chains, 227
 tunneling current, 210
high-frequency molecular devices
 alternating current (AC), 333
 direct current (DC) properties, 333
 dynamic source-drain conductance, 335, 336
 halve-wave rectification, 334, 335
 molecular diodes, 336, 337
 non-equilibrium Green function formalism, 335
highly oriented pyrolytic graphite (HOPG), 151, 323
HOMO–LUMO gap, 11, 69, 120, 142, 227, 233, 234, 238, 251, 255, 256
hopping activation energy, 215
hopping construction mechanism, 167
hydrocarbon chains
 aromatic ring-dominated chains, 229–230
 benzene-dominated chains, 230–234
 conjugated chains, 227–228
 double/triple bond-dominated backbones, 228–229
 saturated, 227
 thiophene-dominated chains, 230
hydrogen bond measurements
 based on GMG-SMJs, 139
 based on STM, 138
hydrogen tautomerization, 286–288
- i***
inelastic electron tunneling spectroscopy (IETS), 27, 38, 157, 377
 advantages, 157
 applications, 163–166
 feature, 161–163
 history, 158–160
 limitations, 165
 measurement, 160–163
integrating molecular functionalities, electrical circuits
- high-frequency molecular devices, 333–337
molecular computing, 306–313
molecular machines
 elevators, 338–341
 molecular motor, 337–338
 nanocar, 344–345
 rotaxane machine, 345–346
 scissors, 341–344
nanocircuits, 225–227
NDC, oscillators
 application of, 276–277
 measurement of, 274–276
 mechanism for, 272–274
rectification/diode
 Aviram–Ratner model, 259–261
D–A diblock molecular system, 263
 Datta–Paulsson model, 259, 262
D– σ –A and D– π –A system, 262–263
gate-controlled single-molecule diode, 272
interfacial coupling, 267–270
 Kornilovitch–Bratkovsky–Williams model, 259, 261
p–n junctions, 258
unimolecular rectification, 271
sensors, 313
single molecules, 225
switches, 284–285
transistors, 277
interband cascade infrared photodetectors (ICIPS), 276
- interfacial coupling**
 contact geometries, 247
 coupling strength and transport mechanism, 249–250
 physical/chemical interactions, 245
- j***
 Johnson–Nyquist noise, 171, 175
- k***
 Kirchhoff's circuit laws, 123
 Kohn–Sham equation, 218, 219
 Kondo blockaded conductance, 127

Kondo effect, 39–40, 125, 126, 128, 214, 279, 281, 302
 Kondo resonance, 11, 40, 125–128, 250
 Koopmans' theory, 185
 Kornilovitch–Bratkovsky–Williams model (KBW), 259, 261
k-point sampling, 216

I

Lagrange multiplier, 216
 Landauer equation, 209, 214
 Landauer formula, 3, 120, 128, 213–215, 220
 Landauer formulism, 214
 Landau levels (LLs), 274–275
 Langmuir–Blodgett films, 263
 laser irradiation, 69
 laser pulse-pair sequence (LPPS), 70
 lead zirconate titanate, 8
 lift-and-float approach, 45–47
 light-triggered switch, 293–297
 liquid metal contact, 45, 47–50
 lithography-defined oxidative cutting process, 98–99
 local density approximation (LDA), 216
 localized molecular orbitals (LMOs), 11, 120, 382
 Lorentz force, 59, 60, 161
 Lorentz function, 211, 213
 Lorentzian distribution noise spectra, 178
 lowest unoccupied molecular orbitals (LUMO), 11, 145, 185, 210, 227
 AR model, 259–261
 conjugated porphyrin arrays, 237–239
 electrochemical gate potential, 301
 electron tunnels, 250
 energy level alignment, 251
 free-base naphthalocyanine, 286–287
 molecule conductance, 245
 π -orbital of, 289
 saturated chains, 227
 tunneling current, 210

m

magic ratio rule (MRR), 120
 mechanical force induced switch, 289–290
 mechanically controllable break junctions (MCBJs), 280, 282
 applications, 25–32
 chip fabrication, 23–25
 electron transport, 26
 spin state control, 26
 surface-enhanced Raman scattering (SERS), 25–26
 technique, 253, 264
 vibrational states, 27
 work principle and advantages, 19–23
 meso–meso linked arrays, 239
 metal containing compounds
 coordination polymers, 237
 oligomers, 235–237
 single molecules, 235–237
 metal-containing covalent bonds, 246
 metal–insulator–adsorbate–metal (MIAM) junctions, 159
 metal–insulator–metal tunnel junctions (MIM-TJs), 130, 131, 172
 metal–molecule–metal junction, 10, 52, 56, 141, 161, 188, 213
 methine carbons, 237
 methyltransferase enzyme, 323
 molecular computing
 DNA-based computing, 306–308
 molecular logic gates, 308–313
 molecular conductance, 142, 145, 165, 236, 239, 245, 247, 248, 250, 256–257, 299, 333
 molecular devices
 addressability, 380
 device fabrication yield, 378
 device-to-device variation and instability, 378–379
 energy consumption, 380
 integration capability, 379
 molecular electronics, 375, 376, 379, 381–384
 carbon nanotubes, 93
 characterizatoin methods, 157–158

- graphene-based electrodes
dash-line lithography (DLL),
103–107
electroburning process, 103
molecular elevators, 337–341
molecular junction
electron transport mechanism, 212
electron-phonon interaction
effects, 214–215
non-idealistic, 212
first-principles modeling
current-voltage characterization,
217–221
density functional theory (DFT),
215–217
tunneling process, 209–212
molecular logic gates, 306, 308–313
molecular machines
elevators, 338–341
molecular motor, 337–338
nanocar, 344–345
rotaxane machine, 345, 346
scissors, 341–344
molecular motor, 337–338, 344, 345
molecular multidot devices, 304
molecular optoelectronics, 17
molecular orbital gating, 34, 190
molecular rectification/diodes
Aviram–Ratner model, 259–261
Datta–Paulsson model, 259, 262
Kornilovitch–Bratkovsky–Williams
model, 259, 261
p-n junctions, 258
stemming from interfacial coupling
anchoring groups, 268–269
contact geometry, 269
electrodes, 267–268
interfacial distance, 269–270
stemming from molecules
D–A diblock molecular system,
263–267
D– σ –A and D– π –A system,
262–263
types of, 271
molecular resonant tunneling diodes
(MRTD), 383
molecular scissors, 341–344
molecular sensors, 225, 313–333
molecular silicon electrodes,
construction of, 114
molecular spin switches, 126
molecular-thickness pentacene, 94
molecular wires, nanocircuits
anchoring groups, 226
backbones, charge transport pathways
biological wires, 241–244
carbon nanotubes, 239–241
hydrocarbon chains, 227–234
metal containing compounds,
234–237
porphyrin arrays, 237–239
single-molecule conductance
definition, 244–245
energy level alignment, 250–252
interfacial coupling, 245–250
molecular conductance, 256–257
photon-assisted conductance
enhancement, 252–256
molecule-electrodes coupling, 215,
252
molecule layer-modified SPM junction,
15
motor drive, 22
- n**
- nanobridge, 24, 31, 32
nanocar, 344, 345
nanocarbon-based molecular
electronics, 321–327
nanocavity plasma enhancement, 131
nanoconstrictions, 174, 376
nanodot, 16
nanogaps, 28, 33, 36, 37, 40, 43, 52–54,
94, 95, 97–99, 103, 104, 114, 115,
165, 178, 377, 381
nanograting, 32
nanolithography, 18, 19
nanometer scale, 17, 18, 37
nanoparticle-based SPM junction, 16
nanopore, 50, 52
nanotransfer imprinting lithographic
(NIL), 54
nanotransfer printing procedure,
54–55

- nanowell, 50–52
- negative differential conductance (NDC)
application of, 276–277
measurement of, 274–276
mechanism for, 273
- negative differential resistance (NDR),
11, 185, 272–274
- noise generation mechanisms, 171
- noise spectroscopy, 180
applications, 174–180
for benzene-dithiol junctions, 179
features, 170
generation-recombination and flicker
noise, 172–173
measurements, 173
shot noise, 171–172
thermal noise, 171–172
- non-covalent interfacial linkages, 245
- non-equilibrium Green's function
(NEGF), 3, 218, 220, 265
- non-Hermitian self-energy matrixes,
219
- non-symmetric diblock
dipyrimidinyldiphenyl
molecules, 264
- nucleophilic substitution reaction,
193, 315, 318
- O**
- 1,8-octanedithiol (ODT), 54, 114, 279
- Ohm's law, 209, 212, 217
- oligo(aryleneethynylene) (OAE) wires,
169
- oligo(phenylene ethylene) (OPE), 123,
230, 232, 233
- oligo(thiophene ethynylene) (OTE),
230
- oligo(thiophene vinylene) (OTV), 230
- oligoarylenes, 229
- oligonaphthalenefluoreneimine (ONI)
molecular wires, 168, 234
- oligophenyleneethynlenes(OPE)–
dithiol/monothiol molecules,
140
- oligophenyleneimine (OPI), 167, 234
- oligothiophenes, 230
- oligoynes, 228, 229
- on-chip electronic–plasmonic
transducers, 130–131
- on-edge molecular junctions (OEMJs),
45, 65–68
- one dimensional (1D) conductance
histogram, 191
- one-dimensional silicon nanowires (1D
SiNWs), 327
- on-wire lithography (OWL), 45,
52–54, 68, 377
- OPE-dithiol molecules, 141
- optical adhesive (OA), 57, 58
- optical and optoelectronic spectroscopy
Raman spectra, 180–182
ultraviolet photoelectron
spectroscopy, 184–185
ultraviolet–visible spectroscopy,
182–183
- X-ray photoelectron spectroscopy,
183–184
- optical lithography, 24, 33, 40, 43, 49,
50
- organic field-effect transistors (OFETs),
94
- oxidation-reduction reaction, 290, 291
- P**
- Peltier cooling, 130
- permethylated α -cyclodextrin
(PM α -CD) molecule, 147
- perylene tetracarboxylic diimide
(PTCDI) molecules, 255
- photochromism, 315, 316
- photoconductance, 252, 254
- photoinduced electron transfer (PET),
243, 309
- photo-induced structural change, 252,
253
- photon-assisted conductance
enhancement, 252–256
- photon-assisted transport (PAT) theory,
31, 69
- piezo actuator, 22, 31
- piezoelectric actuator, 21, 22
- piezoelectric transducer (PZT), 7–8,
19, 20
- π -conjugated backbones, 228

- π -extended tetrathiafulvalene (ex-TTF), 149
 π - π stacking interactions, 140–144, 149
 π -stacked S-OPE3 dimers, 141
plasma-enhanced chemical vapor deposition, 52
Poisson equation, 30, 218, 220
Poisson equations, 30, 218, 220
poly (methyl methacrylate) (PMMA), 18
polymer-assisted lift-off (PALO), 47, 57
polyrotaxane protective sheath, 232
porphyrin arrays, 237–239
porphyrin-fullerene dyad, 152
porphyrinoids, 238, 239
projected density of states (PDOS) calculation, 138
proton-triggered switches, 291, 293
pyridinoparacyclophane (PPC), 190, 292
pyrimidinyl-phenyl diblock co-oligomers, 267
pyrolyzed photoresist films (PPF), 43, 108, 109
pyrroles, 237
pyrrolo-tetrathiafulvalene (pTTF) derivative, 299
- q**
quantum effects, 11, 125, 127, 302
quantum interference (QI), 11–13, 28, 119
chemical design, 124
 π -conducting systems, 120
 π -stacked S-OPE3 dimers, 141
prediction of, 119–120
signature of, 120–123
QuB software, 145, 193
- r**
Raman scattering, 25, 39, 181
Raman spectroscopy, 17
challenges, 182
description, 180–182
uses, 181
- vibrational and electronic heating in the nanoscale junctions, 182
random telegraph noise (RTN), 177–178
Rayleigh scattering, 180
reactive ion etching (RIE), 24, 43, 50, 63
rectification stemming from interfacial coupling anchoring groups, 268–269 contact geometry, 269 electrodes, 267–268 interfacial distance, 269–270 from molecules D–A diblock molecular system, 263–267 D– σ –A and D– π –A system, 262–263 resonant tunneling, 116, 169, 187, 261, 262, 297, 383 room-temperature quantum interference, 221 rotaxane, 149, 291, 340, 345 [2]rotaxane-graphene hybrid optoelectronic device, 148 rotaxane machine, 345, 346
- s**
saturated hydrocarbon chains, 227
scanning probe microscopy (SPM), 2, 7–19
molecule layer-modified, 15
nanoparticle-based, 16
substrate-modified, 15–16
scanning tunneling microscope (STM), 7, 13, 14, 107, 127, 137, 138, 159, 221, 228, 376
scanning tunneling microscopy break junctions (STM-BJs), 127, 147, 228, 255
second-derivative dependency, 216
Seebeck coefficients, 128–133
self-aligned lithography, 45, 60–62
self-assembled monolayers (SAMs), 45, 62, 114, 162, 218, 239, 263, 376
self-breaking method, 30, 35, 36

- sensors
 biological interactions
 nanocarbon-based molecular electronics, 321–327
 silicon-based devices, 327–331
 chemical reactions, 314–319
 conventional, 313
 definition, 313
 electrical, 313
 molecular, 314
 thermoelectrical conversion, 331–333
 sequence-dependent conductance, 242
 shot noise, 171, 172, 177
 measurements, 175
 of tunneling currents, 176
 silicon-based electrodes, 113–116
 silicon nanowires (SiNWs), 61, 138, 327, 328
 silicon RF-Schottky diode architecture, 336
 Simmons equation, 209
 Simmons model, 3, 103, 186, 187, 211, 212
 single-molecule biodetection, 323–325
 single-molecule conductance, 9, 20
 definition, 244–245
 energy level alignment, 250–252
 interfacial coupling, 245–250
 molecular conductance, 256–257
 photon-assisted conductance
 enhancement, 252–256
 single-molecule DNA hybridization dynamics, 138
 single-molecule electronics, goal of, 119
 single-molecule field-effect transistor (FET), 282
 single-molecule junctions, 125
 Coulomb blockade effect, 125
 electrochemical deposition junction, 40, 43
 electromigration breakdown junction, 32–40
 electronic-plasmonic conversion, 130–132
 Kondo effect, 125, 126, 128
 mechanically controllable break junctions (MCBJs), 19–32
 quantum interference effect, 119–120
 scanning probe microscopy break junction, 7–19
 schematic illustration of, 115
 supramolecular interactions, 137
 surface-diffusion-mediated deposition (SDMD) junction, 43–45
 thermoelectricity, 128–130
 single-molecule magnet (SMM) compounds, 302
 single-molecule transistors
 electrochemical gating, 283–284
 side gating, electron transport control, 282–283
 three-terminal electrical devices, 277
 single-nucleotide polymorphisms (SNPs), 242
 single-protein detection, 328
 single-walled carbon nanotubes (SWCNTs), 33, 93, 94, 236, 375
 electrical breakdown, 94–98
 lithography-defined oxidative cutting process, 98–102
 SiNW-FET-based biosensors, 328, 329
 solid-state single-molecule transistors, 278
 source/drain (S/D) electrodes, 94
 spin-cast polymethylmethacrylate layer, 328
 spin-crossover compounds, 126, 303
 spintronics-based switch, 301–305
 spontaneous Raman effect, 180
 squeezable break junction (SBJ), 253
 stereoelectronic effect, 17, 290, 319
 STM-IETS method, 161
 substrate-modified SPM junction, 15–16
 sulfur-free diarylethene molecules, 298

- super-Poissonian shot noise, 172
 supramolecular chemistry, 137
 supramolecular donor-acceptor dyads, 149
 supramolecular interaction, in single-molecule junctions, 137
 charge-transfer interaction, 149–152
 host-guest interaction, 144–149
 hydrogen bonds, 137–139
 π - π stacking interactions, 140–144
 surface-diffusion-mediated deposition (SDMD), 43, 45
 surface-enhanced Raman scattering (SERS), 25–26, 38–39, 161, 181, 182
 surface-enhanced Raman spectroscopy (SERS). *see* surface-enhanced Raman scattering (SERS)
 surface plasmon (SP), 69
 surface plasmon polaritons (SPPs), 31, 130, 253
 suspended-wire molecular junctions (SWMJs), 68, 71
 SWCNT-FET-based single-molecule technique, 321, 322
 switches
 conformational changes
 chemical stimuli triggered switch, 290–293
 electrical field, 285–286
 light-triggered switch, 293–297
 mechanical force induced switch, 289–290
 tunneling electron (charge) triggered switch, 286–289
 electrochemically-gated switch, 297–301
 pressure-driven memory device, 305
 spintronics-based switch, 301–305
 thermal excitation, 305
- t**
 temperature-length-variable transport measurement, 166–170
 terahertz radiation, 27
- tetracyanoquinodimethane (TCNQ), 259
 tetraphenylethene (TPE)-based single-molecule junctions, 143
 1,1'-3,3'-tetrasubstituted ferrocene, 342
 tetrathiafulvalene–tetracyanoquinodimethane (TTF-TCNQ) systems, 149, 150
 tetrathiofulvalene (TTF), 259
 thermal evaporation, 376
 thermally-assisted hopping mechanism, 169
 thermal noise, 171
 thermoelectricity, 128
 thermopower, 28, 30
 thiophene-based materials, 152
 thiophene-1,1-dioxide (TDO), 272
 thiophene-dominated chains, 230
 three-terminal nuclear spin quantum bit transistor, 126
 Tien–Gordon model, 254
 time-dependent Nernst–Planck, 30
 time-independent Schrödinger, 210
 transfer printing techniques, 54, 60
 transistors
 back gate, 277
 carbon electrode–molecule junctions, 277
 electromigration break junctions, 277
 transition voltage spectroscopy (TVS), 186, 187
 applications, 188–191
 Au–vacuum–Au junctions, 190
 effectiveness, 186
 interface-related properties, 189
 using Taylor expansion view, 188
 transmission electron microscopy (TEM), 282
 4,4''-tribenzenedithiol, 129
 thermoelectricity properties of, 129
 tunneling barrier height, 167
 tunneling current density, 211

tunneling electron (charge) triggered switch, 286
tunneling mechanism, 167
tunneling process, 209
two-dimensional (2D) conductance histogram, 191, 192

U

ultraviolet irradiation, 377
ultraviolet photoelectron spectroscopy (UPS), 184–185
ultraviolet-visible spectroscopy (UV-Vis), 182–183
unimolecular rectification, 263, 271
UV-Vis spectrophotometer, 183

V

valence-conversional molecules, 126
van der Waals binding, 245
van der Waals forces, 15, 98
van der Waals' interactions, 10

visible light irradiation, 164, 377
voltage-induced conductivity switch, 126

W

Watson–Crick complementary, 306, 307
Wentzel–Kramers–Brillouin (WKB) approximation, 209
wet etching techniques, 50
working electrodes (WE), 40, 41, 283, 298

X

X-ray photoelectron spectroscopy, 54, 183–184
X-ray spectroscopy, 377

Z

zinc porphyrin, 343, 344